

2SC3503/KSC3503

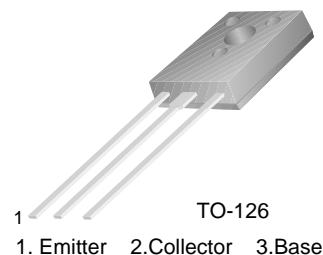
NPN Epitaxial Silicon Transistor

Applications

- Audio, Voltage Amplifier and Current Source
- CRT Display, Video Output
- General Purpose Amplifier

Features

- High Voltage : $V_{CEO} = 300V$
- Low Reverse Transfer Capacitance : $C_{re} = 1.8pF$ at $V_{CB} = 30V$
- Excellent Gain Linearity for low THD
- High Frequency: 150MHz
- Full thermal and electricalSpice models are available
- Complement to 2SA1381/KSA1381.



Absolute Maximum Ratings* $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CBO}	Collector-Base Voltage	300	V
BV_{CEO}	Collector-Emitter Voltage	300	V
BV_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current(DC)	100	mA
I_{CP}	Collector Current(Pulse)	200	mA
P_C	Total Device Dissipation, $T_C=25^\circ C$ $T_C=125^\circ C$	7 1.2	W W
T_J, T_{STG}	Junction and Storage Temperature	- 55 ~ +150	$^\circ C$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* $T_a=25^\circ C$ unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	17.8	$^\circ C/W$

* Device mounted on minimum pad size

h_{FE} Classification

Classification	C	D	E	F
h_{FE}	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320

Electrical Characteristics* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	300			V
BV_{CEO}	Collector- Emitter Breakdown Voltage	$I_C = 1\text{mA}, I_B = 0$	300			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	5			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 200\text{V}, I_E = 0$			0.1	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 4\text{V}, I_C = 0$			0.1	μA
h_{FE}	DC Current Gain	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	40		320	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 20\text{mA}, I_B = 2\text{mA}$			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 20\text{mA}, I_B = 2\text{mA}$			1	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 30\text{V}, I_C = 10\text{mA}$		150		MHz
C_{ob}	Output Capacitance	$V_{CB} = 30\text{V}, f = 1\text{MHz}$		2.6		pF
C_{re}	Reverse Transfer Capacitance	$V_{CB} = 30\text{V}, f = 1\text{MHz}$		1.8		pF

* Pulse Test: Pulse Width \leq 300 μs , Duty Cycles \leq 2%**Ordering Information**

Part Number*	Marking	Package	Packing Method	Remarks
2SC3503CSTU	2SC3503C	TO-126	TUBE	hFE1 C grade
2SC3503DSTU	2SC3503D	TO-126	TUBE	hFE1 D grade
2SC3503ESTU	2SC3503E	TO-126	TUBE	hFE1 E grade
2SC3503FSTU	2SC3503F	TO-126	TUBE	hFE1 F grade
KSC3503CSTU	C3503C	TO-126	TUBE	hFE1 C grade
KSC3503DSTU	C3503D	TO-126	TUBE	hFE1 D grade
KSC3503ESTU	C3503E	TO-126	TUBE	hFE1 E grade
KSC3503FSTU	C3503F	TO-126	TUBE	hFE1 F grade

* 1. Affix "-S-" means the standard TO126 Package.(see package dimensions). If the affix is "-STS-" instead of "-S-", that mean the short-lead TO126 package.
 2. Suffix "-TU" means the tube packing. The Suffix "TU" could be replaced to other suffix character as packing method.

Typical Characteristics

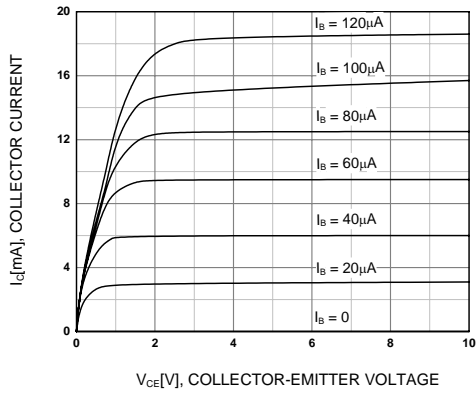


Figure 1. Static Characteristic

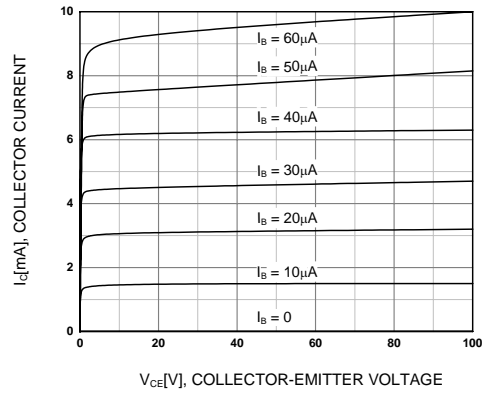


Figure 2. Static Characteristic

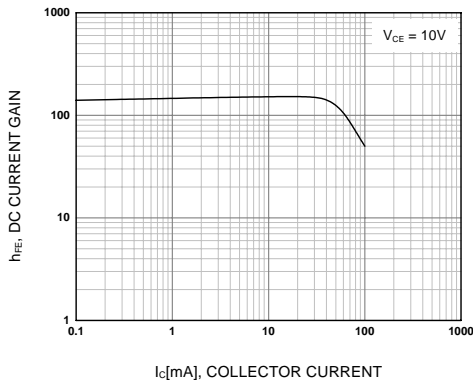


Figure 3. DC current Gain

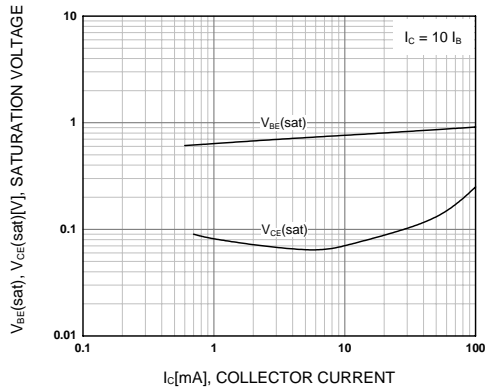


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

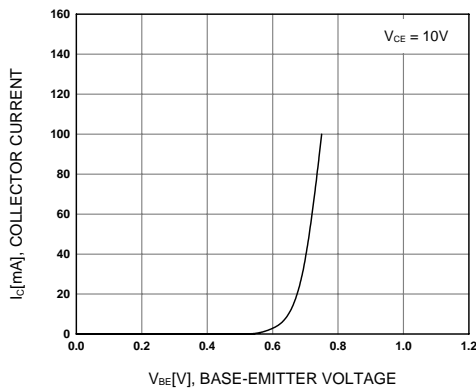


Figure 5. Base-Emitter On Voltage

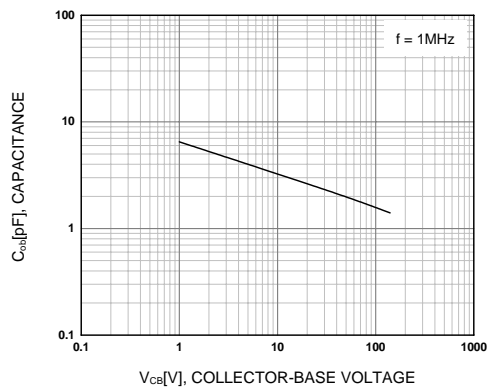


Figure 6. Collector Output Capacitance

Typical Characteristics (Continued)

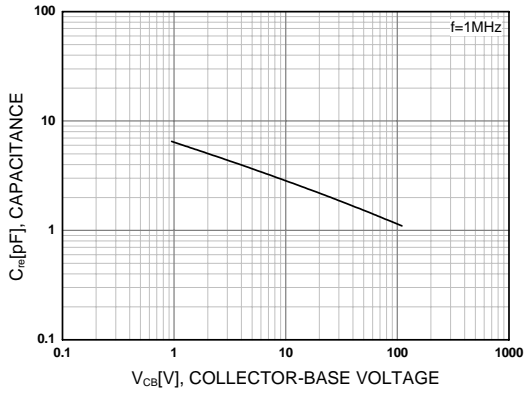


Figure 7. Reverse Transfer Capacitance

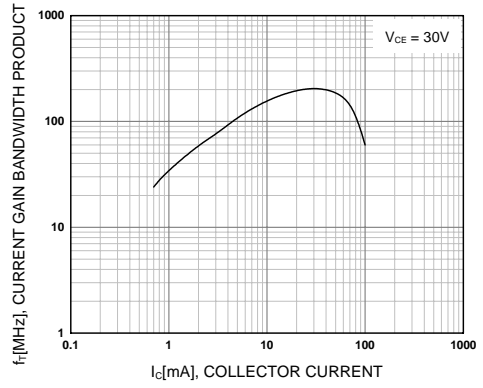


Figure 8. Current Gain Bandwidth Product

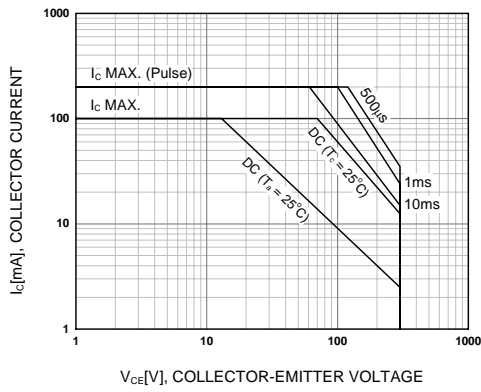


Figure 9. Safe Operating Area

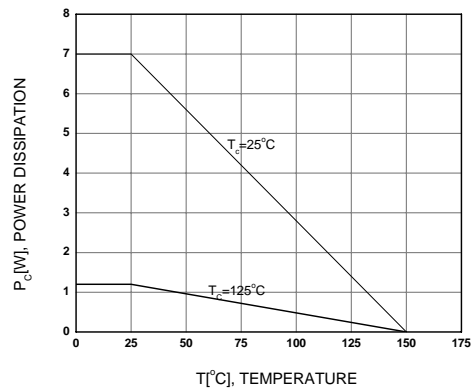
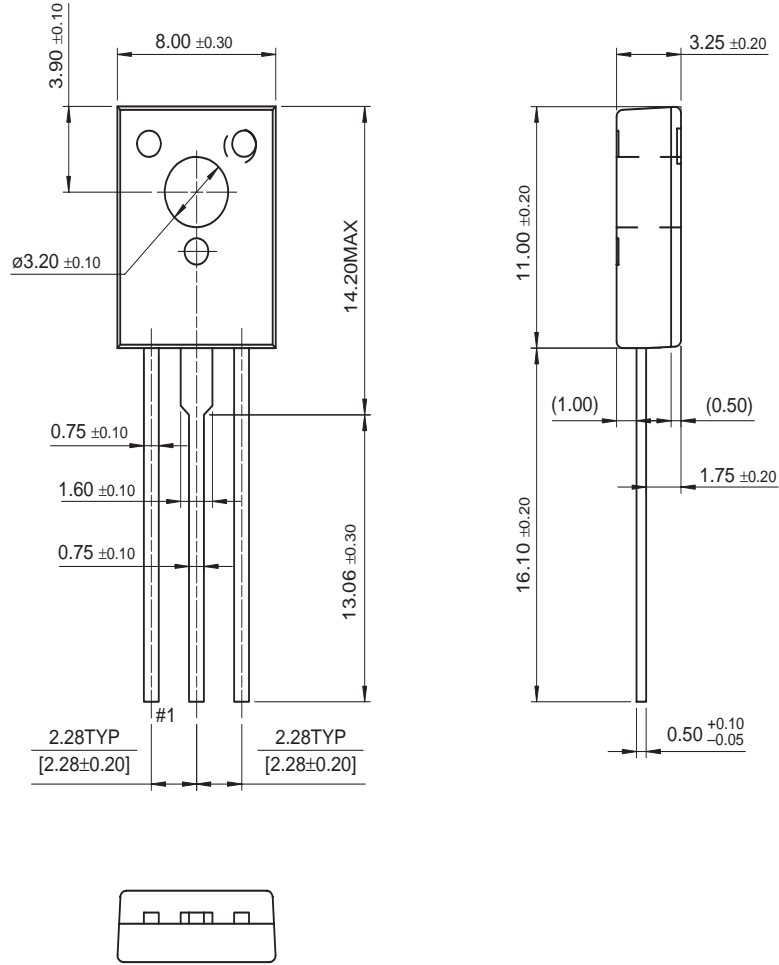


Figure 10. Power Derating

Package Dimensions

TO-126



Dimensions in Millimeters



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CTL™	IntelliMAX™	Programmable Active Droop™	TinyBoost™
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EcoSPARK®	MegaBuck™	QS™	TinyLogic®
	MICROCOUPLER™	QT Optoelectronics™	TinyOPTO™
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FACT®	Motion-SPM™	SPM®	μSerDes™
FAST®	OPTOLOGIC®	STEALTH™	UHC®
FastvCore™	OPTOPLANAR®	SuperFET™	UniFET™
FPST™		SuperSOT™-3	VCX™
FRFET®	PDP-SPM™	SuperSOT™-6	
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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